

KSB1023

Power Amplifier Applications

- High DC Current Gain
- WWW.DISC.COM Low Collector-Emitter Saturation Voltage
- Complement to KSD1413



2.Collector 3.Emitter WWW.DZSC.CO

PNP Silicon Darlington Transistor

Absolute Maximum Ratings T_C=25°C unless otherwise noted

| Symbol Parameter | | Value | Units |
|------------------|--|------------|-------|
| V _{CBO} | Collector-Base Voltage | - 60 | V |
| V _{CEO} | Collector-Emitter Voltage | - 40 | V |
| V _{EBO} | Emitter-Base Voltage | - 5 | V |
| I _C | Collector Current (DC) | - 3 | А |
| I _{CP} | Collector Current (Pulse) | - 6 | А |
| I _B | Base Current | - 0.3 | A |
| P _C | Collector Dissipation (T _a =25°C) | 2 | W |
| P _C | Collector Dissipation (T _C =25°C) | 20 | W |
| TJ | Junction Temperature | 150 | °C |
| T _{STG} | Storage Temperature | - 55 ~ 150 | °C |

Electrical Characteristics T_C=25°C unless otherwise noted

| Symbol | Parameter | Test Condition | Min. | Тур. | Max. | Units |
|--------------------------------------|--------------------------------------|--|--------------|------|-------|-------|
| BV _{CEO} | Collector-Emitter Breakdown Voltage | $I_C = -25 \text{mA}, I_B = 0$ | - 40 | | | V |
| I _{CBO} | Collector Cut-off Current | $V_{CB} = -60V, I_{E} = 0$ | | | - 20 | μΑ |
| I _{EBO} | Emitter Cut-off Current | $V_{EB} = -5V, I_{C} = 0$ | | | - 2.5 | mA |
| h _{FE1} h _{FE2} | DC Current Gain | V _{CE} = - 2V, I _C = - 1A V _{CE} = - 2V, I _C = - 3A | 2000 1000 | | Z-75 | TOY |
| V _{CE} (sat) | Collector-Emitter Saturation Voltage | $I_C = -2A$, $I_B = -4mA$ | | | - 1.5 | V |
| V _{BE} (sat) | Base-Emitter Saturation Voltage | $I_C = -2A$, $I_B = -4mA$ | HE | W W | - 2 | V |
| t _{ON} | Turn ON Time | $V_{CC} = -30V, I_{C} = -3A$ $I_{B1} = -I_{B2} = -6mA$ | 1 1 1 - 1 | 0.3 | | μs |
| t _{STG} | Storage Time | | | 0.6 | | μs |
| t _F | Fall Time | $R_L = 10\Omega$ | | 0.25 | | μs |
| 44 | WWW.DZSC.CO | | | | | |

Typical Characteristics

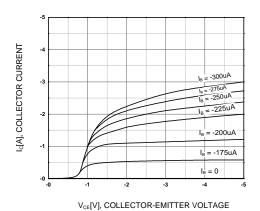


Figure 1. Static Characteristic

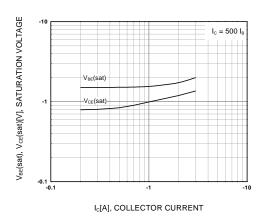


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturating Voltage

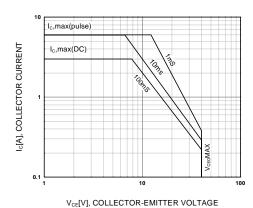
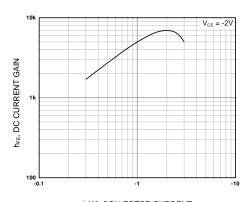


Figure 5. Safe Operating Area



 $I_{c}[A]$, COLLECTOR CURRENT

Figure 2. DC current Gain

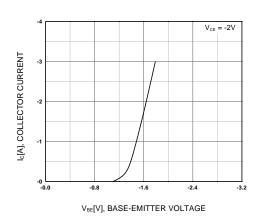


Figure 4. Base-Emitter On Voltage

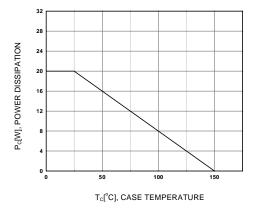
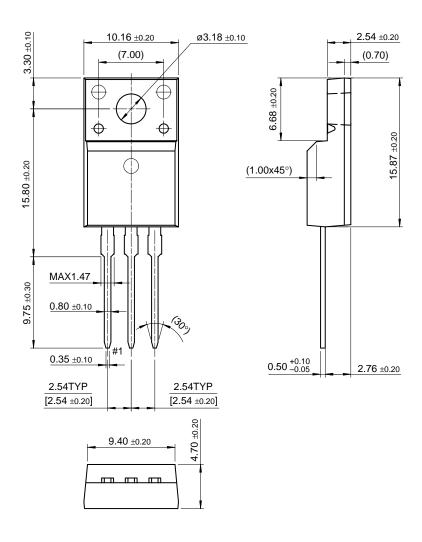


Figure 6. Power Derating

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Package Demensions

TO-220F



Dimensions in Millimeters

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